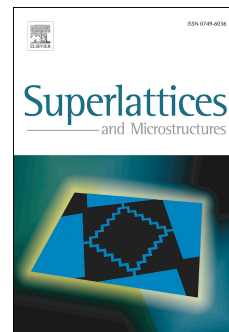


Accepted Manuscript

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PII: S0749-6036(18)30634-7

DOI: [10.1016/j.spmi.2018.04.018](https://doi.org/10.1016/j.spmi.2018.04.018)

Reference: YSPMI 5632

To appear in: *Superlattices and Microstructures*

Received Date: 29 March 2018

Revised Date: 8 April 2018

Accepted Date: 8 April 2018

Please cite this article as: H.V. Phuc, N.N. Hieu, V.V. Ilyasov, L.T.T. Phuong, C.V. Nguyen, First principles study of the electronic properties and band gap modulation of two-dimensional phosphorene monolayer: Effect of strain engineering, *Superlattices and Microstructures* (2018), doi: 10.1016/j.spmi.2018.04.018.

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First principles study of the electronic properties and band gap modulation of two-dimensional phosphorene monolayer: Effect of strain engineering

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Abstract

The effect of strain on the structural and electronic properties of monolayer phosphorene is studied by using first-principle calculations based on the density functional theory. The intra- and inter-bond length and bond angle for monolayer phosphorene is also evaluated. The intra- and inter-bond length and the bond angle for phosphorene show an opposite tendency under different directions of the applied strain. At the equilibrium state, monolayer phosphorene is a semiconductor with a direct band gap at the Γ -point of 0.91 eV. A direct-indirect band gap transition is found in monolayer phosphorene when both the compression and tensile strain are simultaneously applied along both zigzag and armchair directions. Under the applied compression strain, a semiconductor-metal transition for monolayer phosphorene is observed at -13% and -10% along armchair and zigzag direction, respectively.

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